

	L #	Hits	Search Text	DBs
1	L1	169659	"438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	L2	810	1 and (SOI or silicon-on-insulator) near (transistor or MOSFET or FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	L3	4	2 and (body near contact?) and ((first and second) near isolat\$)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	L4	1	2 and (body near contact?) and (gate near extension)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	L5	77	(liu-yowjuang-w or liang-minchang).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	L7	0	5 and (body near contact?) and ((first and second) near isolat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	L8	385	(body near contact?).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	L10	0	9 and (first and second) near (isolat\$3 or (gate near extension))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	L9	7	8 and (SOI or silicon-on-insulator) near (transistor or MOSFET or FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	L11	5	((SOI or silicon-on-insulator) near (transistor or MOSFET or FET)) and (body near contact?) and ((first and second) near ((source and isolation) or (gate near extension)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB